

Hyperfast power diode Rev. 01 — 27 December 2010

Product data sheet

Product profile 1.

1.1 General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

1.2 Features and benefits

- Isolated plastic package
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

1.3 Applications

Continuous Current Mode (CCM) Power Factor Correction (PFC)

- Half-bridge/full-bridge switched-mode power supplies
- Half-bridge lighting ballasts

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; $\bar{\delta}$ = 0.5; T_h = 47 °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	8	Α
Static char	acteristics					
V _F	forward voltage	$I_F = 8 \text{ A}; T_j = 150 \text{ °C};$ see Figure 4	-	1.5	1.85	V
		I _F = 8 A; T _j = 25 °C	-	2	2.9	V
Dynamic c	haracteristics					
t _{rr}	reverse recovery time	$I_F = 8 \text{ A}; V_R = 400 \text{ V};$ $dI_F/dt = 500 \text{ A}/\mu\text{s}; T_j = 25 \text{ °C};$ see Figure 5	-	20	-	ns



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	Α	anode	mb	K
mb	n.c.	mounting base; isolated		
			SOD113 (TO-220F)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYC8DX-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; δ = 0.5 ; T _h = 47 °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	8	Α
I _{FRM}	repetitive peak forward current	square-wave pulse; $\delta = 0.5$; $t_p = 25~\mu s;$ $T_h = 47~^{\circ} C$	-	16	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C	-	55	Α
		t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C	-	60	Α
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

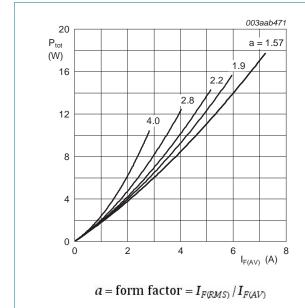
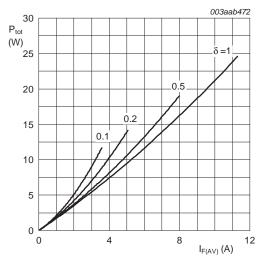


Fig 1. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



 $I_{F(AV)} = I_{F(RMS)} imes \sqrt{oldsymbol{\delta}}$

Fig 2. Forward power dissipation as a function of average forward current; square waveform; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	without heatsink compound	-	-	7.2	K/W
		with heatsink compound; see Figure 3	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air		-	60	-	K/W

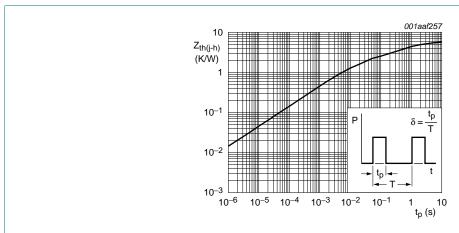


Fig 3. Transient thermal impedance from junction to heatsink as a function of pulse width

6. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz ; from cathode to external heatsink	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	cteristics					
V _F	forward voltage	$I_F = 8 \text{ A}$; $T_j = 150 ^{\circ}\text{C}$; see Figure 4	-	1.5	1.85	V
		I _F = 8 A; T _j = 25 °C	-	2	2.9	V
I _R	reverse current	V _R = 500 V; T _j = 100 °C	-	1.1	3	mA
		V _R = 600 V	-	9	40	μΑ
Dynamic cha	aracteristics					
Q _r	recovered charge	$I_F = 1 \text{ A}; V_R = 100 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	13	-	nC
t _{rr}	reverse recovery time	$I_F = 8 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 500 \text{ A/}\mu\text{s}$; $T_j = 100 \text{ °C}$	-	32	40	ns
		$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$	-	30	52	ns
		$I_F = 8 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 500 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 5	-	20	-	ns
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s}; $ $T_j = 100 \text{ °C}$	-	9.5	12	Α
		$I_F = 8 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 50 \text{ A/}\mu\text{s}$; $T_j = 125 \text{ °C}$	-	1.5	5.5	Α
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 6	-	8	10	V

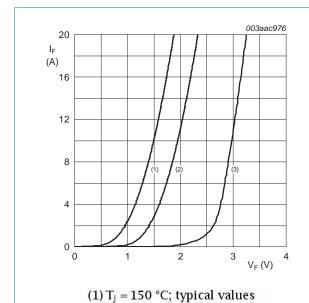


Fig 4. Forward current as a function of forward voltage

(2) $T_j = 150$ °C; maximum values (3) $T_j = 25$ °C; maximum values

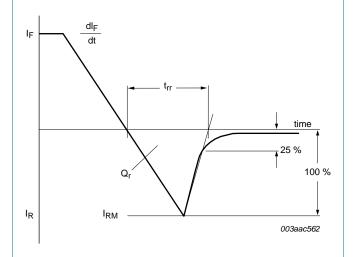
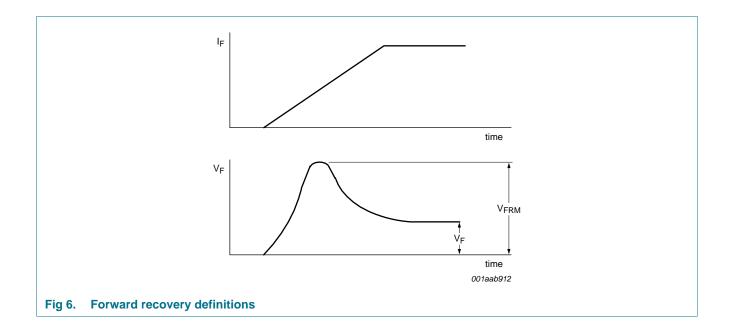


Fig 5. Reverse recovery definitions; ramp recovery



8. Package outline

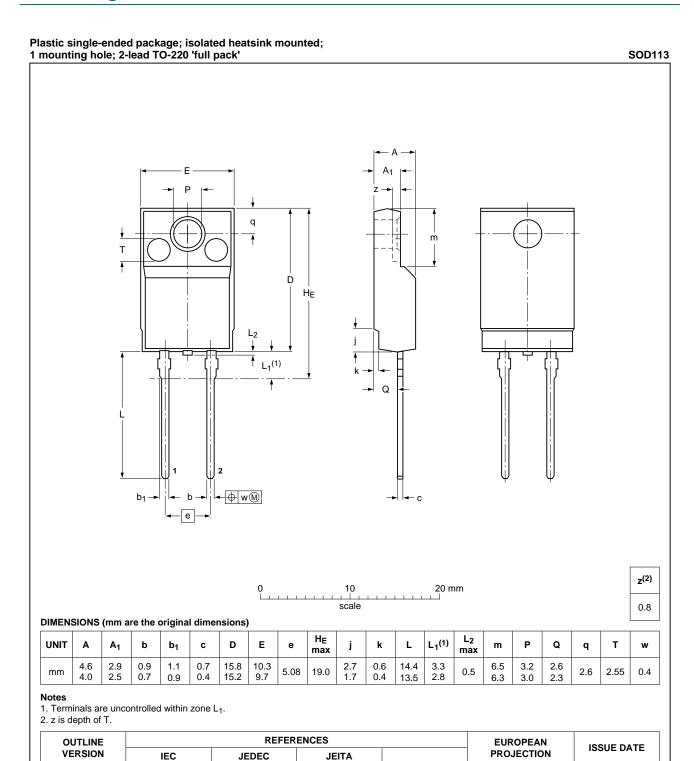


Fig 7. Package outline SOD113 (TO-220F)

BYC8DX-600

2-lead TO-220F

02-04-09

07-06-18

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SOD113

BYC8DX-600

Hyperfast power diode

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYC8DX-600 v.1	20101227	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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